

AMENDMENTS TO THE SPECIFICATION:

Please add the following new paragraphs on page 15 after line 11:

Figure 12A shows the [011] direction and the (100) plane relative to a substrate unit cell.

Figure 12B is a top view of the crystal substrate showing [011] direction and the (100) plane.

Figure 12C is a side view of a substrate having an 8° to 20° incline in the [011] direction.

Please amend the paragraph beginning at page 22, line 15, as follows:

In a preferred embodiment of the present invention, crystal of the substrate is inclined by about 8° (8 degrees) to about 20° (20 degrees) in a [011] direction with respect to a (100) plane (see Figures 12A-12C). Therefore, when an $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ current diffusion layer with a thickness of about 5 to 10 μm which lattice-mismatches with a light-emitting structure is to be grown on a light-emitting structure, a hillock is not generated (which is otherwise generated due to lattice mismatching), so that a flat current diffusion layer can be obtained.